

# **PSMN057-200B**

## N-channel TrenchMOS SiliconMAX standard level FET **Product data sheet**

#### 1. **General description**

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

#### 2. **Features and benefits**

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

## **Applications**

- DC-to-DC converters
- Switched-mode power supplies

## Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	200	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C		-	-	39	Α
P <sub>tot</sub>	total power dissipation			-	-	250	W
Static charact	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 17 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	41	57	mΩ
Dynamic characteristics							
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 10 V; $I_D$ = 39 A; $V_{DS}$ = 160 V; $T_j$ = 25 °C		-	37	50	nC



## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain		
3	S	source		G
mb	D	mounting base; connected to drain	1 3	mbb076 S
			D2PAK (SOT404)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PSMN057-200B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN057-200B	PSMN057-200B

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	200	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ	-	200	V
$V_{GS}$	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 100 °C	-	27.5	Α
		T <sub>mb</sub> = 25 °C	-	39	Α
I <sub>DM</sub>	peak drain current	pulsed; T <sub>mb</sub> = 25 °C	-	156	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	250	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
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Symbol	Parameter	Conditions	Min	Max	Unit
Source-dra	in diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	39	Α
I <sub>SM</sub>	peak source current	pulsed; T <sub>mb</sub> = 25 °C	-	156	Α
Avalanche	ruggedness		l		
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 35 A; $V_{sup} \le 50$ V; unclamped; $t_p$ = 100 μs; $R_{GS}$ = 50 $\Omega$	-	300	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup} \le 50$ V; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $R_{GS}$ = 50 Ω; unclamped	-	35	Α

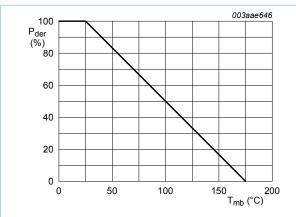


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

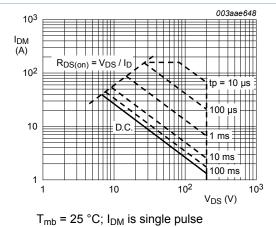


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

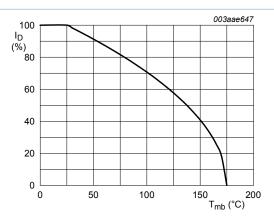
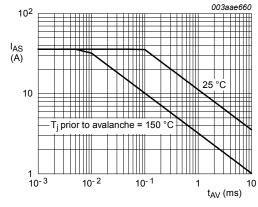


Fig. 2. Normalized continuous drain current as a function of mounting base temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$



unclamped inductive load

ig. 4. Single-shot avalanche rating; avalanche current as a function of avalanche period

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## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base		-	-	0.6	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; FR4 board	-	50	-	K/W

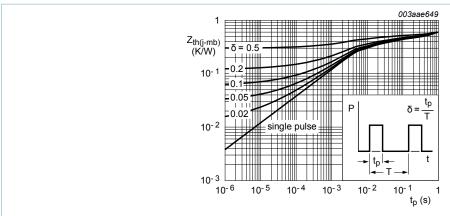


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics		'			
V <sub>(BR)DSS</sub>	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	200	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$	178	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 ^{\circ}\text{C}$	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	4.4	V
I <sub>DSS</sub> drain leakage curre	drain leakage current	V <sub>DS</sub> = 200 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μΑ
		V <sub>DS</sub> = 200 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.03	10	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 17 A; T <sub>j</sub> = 175 °C	-	-	165	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 17 A; T <sub>j</sub> = 25 °C	-	41	57	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_G$	internal gate resistance (AC)	f = 1 MHz	-	2	4.1	Ω
Dynamic ch	naracteristics				'	
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 39 A; V <sub>DS</sub> = 160 V; V <sub>GS</sub> = 10 V;	-	96	135	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	13	-	nC
$Q_{GD}$	gate-drain charge		-	37	50	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	3750	5036	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	385	520	pF
C <sub>rss</sub>	reverse transfer capacitance		-	180	252	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 100 V; $R_L$ = 2.7 $\Omega$ ; $V_{GS}$ = 10 V;	-	18	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 °C$	-	58	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	105	-	ns
t <sub>f</sub>	fall time		-	78	-	ns
L <sub>D</sub>	internal drain inductance	measured from tab to centre of die ; $T_j = 25 ^{\circ}\text{C}$	-	3.5	-	nΗ
L <sub>S</sub>	internal source inductance	measured from source lead to source bond pad; $T_j = 25$ °C	-	7.5	-	nH
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	133	173	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	895	-	nC

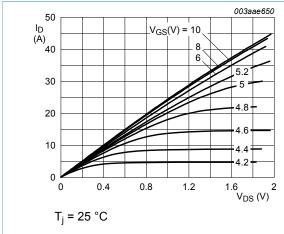


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

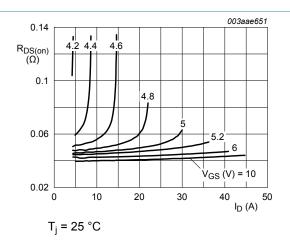


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values

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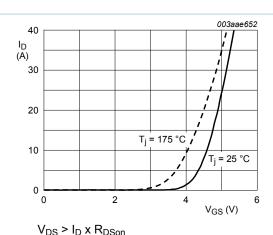
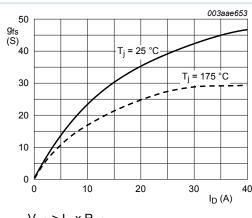


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$ 

Fig. 9. Forward transconductance as a function of drain current; typical values

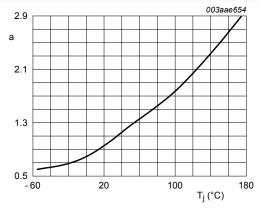
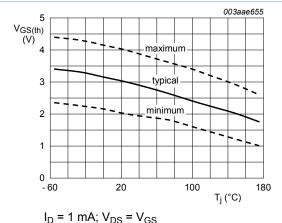
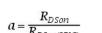


Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature







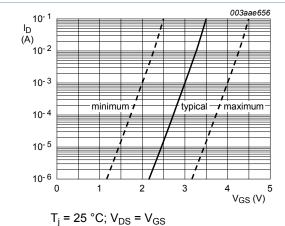
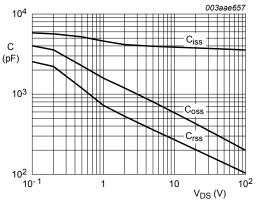


Fig. 12. Sub-threshold drain current as a function of gate-source voltage



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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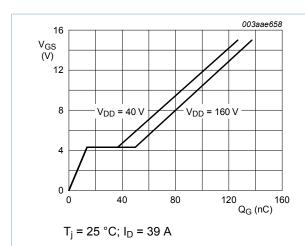


Fig. 14. Gate-source voltage as a function of gate charge; typical values

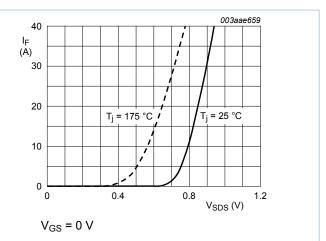
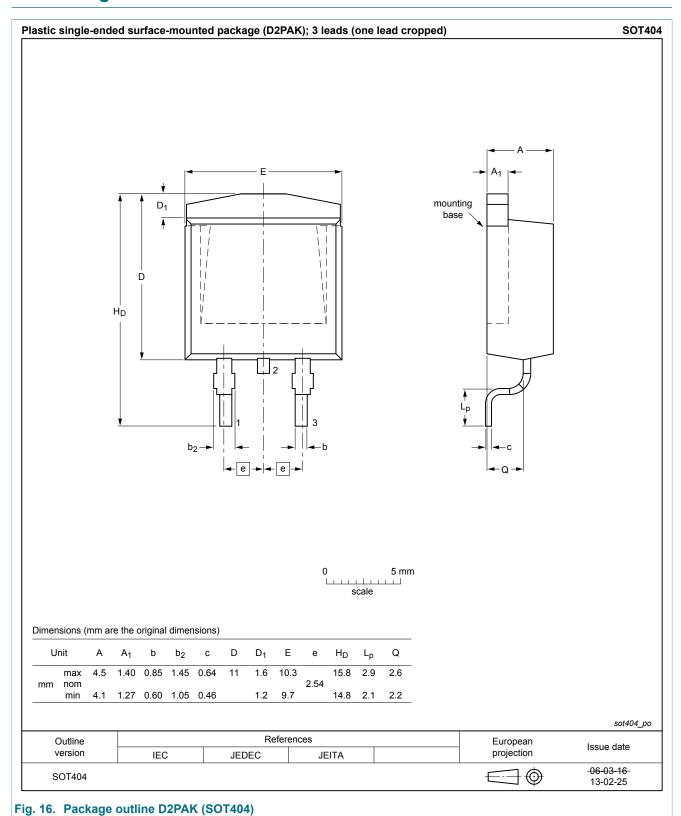


Fig. 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

## 11. Package outline



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## 12. Legal information

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